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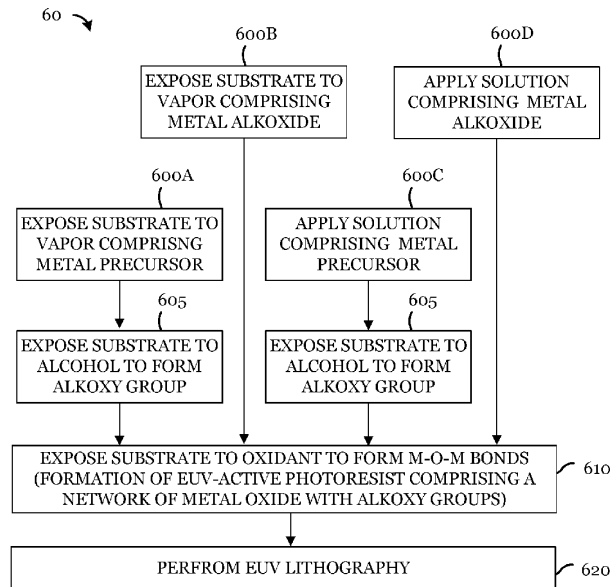


FIG. 6A

(57) Abstract: A method of processing a substrate that includes forming over the substrate an extreme ultraviolet (EUV)-active photoresist film including a network of metal oxide terminated with alkoxy groups and patterning the EUV-active photoresist film with EUV lithography.

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